

1 Electrical ratings

Table 1. Absolute maximum ratings

| Cumbal | Davamatar | | Value | Unit |
|--------------------------------|--|--------------------|---------------------|------|
| Symbol | Parameter | TO-220FP | I²PAK, TO-220, IPAK | Unit |
| V_{DS} | Drain-source voltage | | 600 | V |
| V _{GS} | Gate-source voltage | | ±25 | V |
| | Drain current (continuous) at T _C = 25 °C | 11 ⁽¹⁾ | 11 | |
| I _D | Drain current (continuous) at T _C = 100 °C | 6.9 ⁽¹⁾ | 6.9 | _ A |
| I _{DM} ⁽²⁾ | Drain current pulsed | 44(1) | 44 | Α |
| P _{TOT} | Total power dissipation at T _C = 25 °C | 25 90 | | W |
| dv/dt ⁽³⁾ | Peak diode recovery voltage slope | | 15 | V/ns |
| V _{ISO} | Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T_C = 25 $^{\circ}C$) | 2.5 | | kV |
| T_J | Operating junction temperature range | , | | °C |
| T _{stg} | Storage temperature range | | -55 to 150 | |

- 1. Limited by maximum junction temperature.
- 2. Pulse width limited by safe operating area.
- 3. $I_{SD} \le 11~A$, $di/dt \le 400~A/\mu s$, $V_{DD} = 80\%~V_{(BR)DSS}$.

Table 2. Thermal data

| Symbol | Parameter | Value | | | |
|-----------------------|-------------------------------------|----------|---------------|------|------|
| Symbol | | TO-220FP | I²PAK, TO-220 | IPAK | Unit |
| R _{thj-case} | Thermal resistance junction-case | 5 1.39 | | | °C/W |
| R _{thj-a} | Thermal resistance junction-ambient | 62.5 | | 100 | °C/W |

Table 3. Avalanche characteristics

| Symbol | Parameter | Value | Unit |
|-----------------|---|-------|------|
| I _{AS} | Avalanche current, repetitive or not repetitive (pulse width limited by T_J max) | 3.5 | Α |
| E _{AS} | Single-pulse avalanche energy (starting $T_J = 25 ^{\circ}\text{C}$, $I_D = I_{AS}$, $V_{DD} = 50 \text{V}$) | 200 | mJ |

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2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4. Static

| Symbol | Parameter | Test conditions | Min. | Тур. | Max. | Unit |
|----------------------|--|---|------|------|------|------|
| V _{(BR)DSS} | Drain-source breakdown voltage | V _{GS} = 0 V, I _D = 1 mA | 600 | | | V |
| I | Zono moto vielto no duois oviment | V _{GS} = 0 V, V _{DS} = 600 V | | | 1 | |
| IDSS | I _{DSS} Zero gate voltage drain current | V_{GS} = 0 V, V_{DS} = 600 V, T_{C} = 125 °C ⁽¹⁾ | | | 100 | μA |
| I _{GSS} | Gate-body leakage current | V _{DS} = 0 V, V _{GS} = ±25 V | | | ±100 | nA |
| V _{GS(th)} | Gate threshold voltage | V _{DS} = V _{GS} , I _D = 250 μA | 2 | 3 | 4 | V |
| R _{DS(on)} | Static drain-source on-resistance | V _{GS} = 10 V, I _D = 5.5 A | | 280 | 360 | mΩ |

^{1.} Defined by design, not subject to production test.

Table 5. Dynamic

| Symbol | Parameter Test conditions | | Min. | Тур. | Max. | Unit |
|------------------|-------------------------------|---|------|------|------|------|
| C _{iss} | Input capacitance | | - | 790 | - | pF |
| C _{oss} | Output capacitance | V _{DS} = 50 V, f = 1 MHz, V _{GS} = 0 V | | 60 | - | pF |
| C _{rss} | Reverse transfer capacitance | | | 3.6 | - | pF |
| Coss eq. (1) | Equivalent output capacitance | V _{DS} = 0 to 480 V, V _{GS} = 0 V | - | 135 | - | pF |
| Qg | Total gate charge | V _{DD} = 480 V, I _D = 11 A, V _{GS} = 0 to 10 V | - | 27 | - | nC |
| Q _{gs} | Gate-source charge | (see Figure 17. Test circuit for gate | - | 4 | - | nC |
| Q _{gd} | Gate-drain charge | charge behavior) | | 14 | - | nC |
| R _g | Gate input resistance | f = 1 MHz, open drain | - | 4.7 | - | Ω |

^{1.} $C_{\text{oss eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

| Symbol | Parameter | Test conditions | Min. | Тур. | Max. | Unit |
|---------------------|---------------------|---|------|------|------|------|
| t _{d(on)} | Turn-on delay time | V _{DD} = 300 V, I _D = 5.5 A, | - | 3 | - | ns |
| t _r | Rise time | $R_G = 4.7 \Omega, V_{GS} = 10 V$ | - | 8 | - | ns |
| t _{d(off)} | Turn-off delay time | (see Figure 16. Test circuit for resistive load switching times and | - | 30 | - | ns |
| t _f | Fall time | Figure 21. Switching time waveform) | - | 10 | - | ns |

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Table 7. Source-drain diode

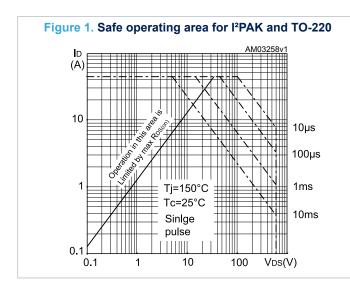
| Symbol | Parameter | Test conditions | Min. | Тур. | Max. | Unit |
|---------------------------------|-------------------------------|---|------|------|------|------|
| I _{SD} | Source-drain current | | - | | 11 | Α |
| I _{SDM} ⁽¹⁾ | Source-drain current (pulsed) | | - | | 44 | Α |
| V _{SD} (2) | Forward on voltage | V _{GS} = 0 V, I _{SD} = 11 A | - | | 1.5 | V |
| t _{rr} | Reverse recovery time | I _{SD} = 11 A, di/dt = 100 A/μs, | - | 230 | | ns |
| Q _{rr} | Reverse recovery charge | V _{DD} = 100 V | - | 2 | | μC |
| I _{RRM} | Reverse recovery current | (see Figure 18. Test circuit for inductive load switching and diode recovery times) | - | 18 | | Α |
| t _{rr} | Reverse recovery time | I _{SD} = 11 A, di/dt = 100 A/µs, | - | 290 | | ns |
| Qrr | Reverse recovery charge | V _{DD} = 100 V, T _J = 150 °C | - | 2.5 | | μC |
| I _{RRM} | Reverse recovery current | (see Figure 18. Test circuit for inductive load switching and diode recovery times) | - | 17 | | Α |

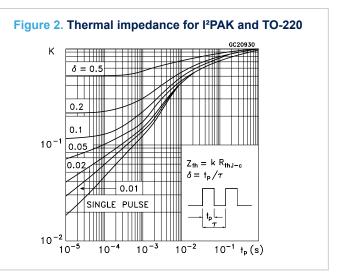
^{1.} Pulse width is limited by safe operating area.

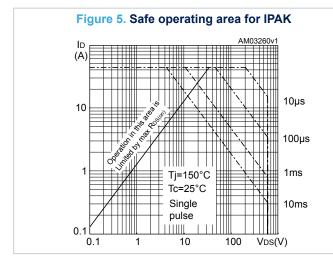
^{2.} Pulse test: pulse duration = $300 \mu s$, duty cycle 1.5%.

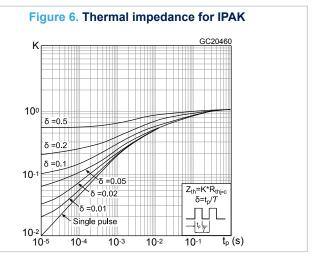


2.1 Electrical characteristics (curves)









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Figure 7. Output characteristics

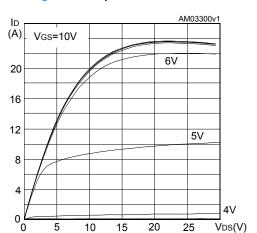


Figure 8. Transfer characteristics

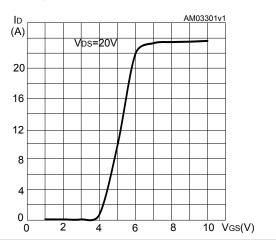


Figure 9. Normalized V_{DS} vs temperature

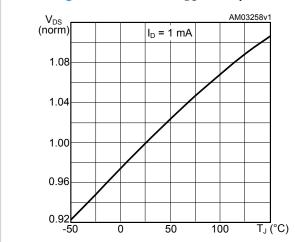


Figure 10. Static drain-source on-resistance

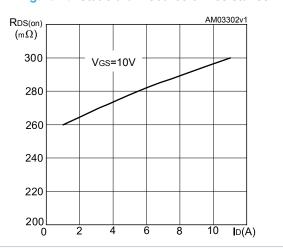


Figure 11. Gate charge vs gate-source voltage

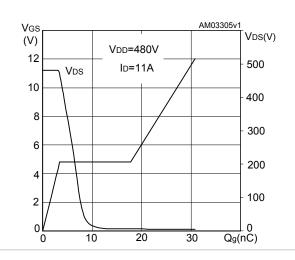
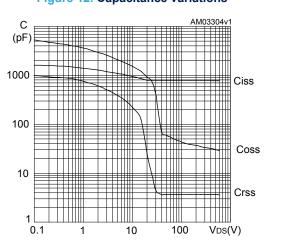


Figure 12. Capacitance variations



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Figure 13. Normalized gate threshold voltage vs temperature

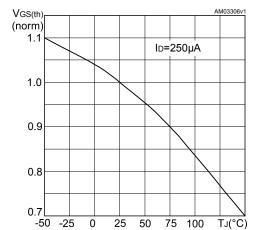
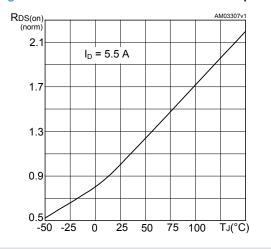
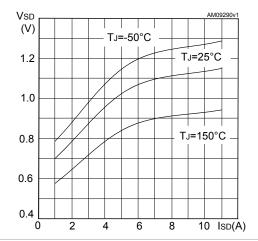


Figure 14. Normalized on resistance vs temperature







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AM01469v1



3 Test circuits

Figure 16. Test circuit for resistive load switching times

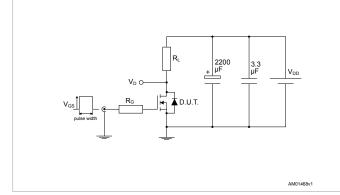


Figure 17. Test circuit for gate charge behavior

Figure 18. Test circuit for inductive load switching and diode recovery times

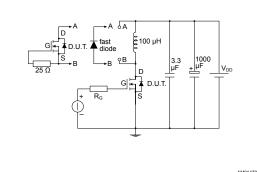


Figure 19. Unclamped inductive load test circuit

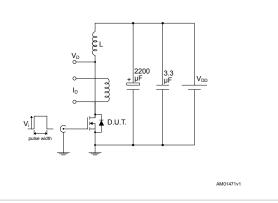


Figure 20. Unclamped inductive waveform

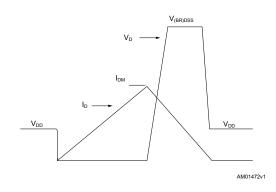
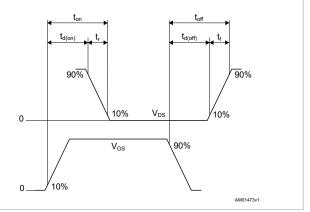


Figure 21. Switching time waveform



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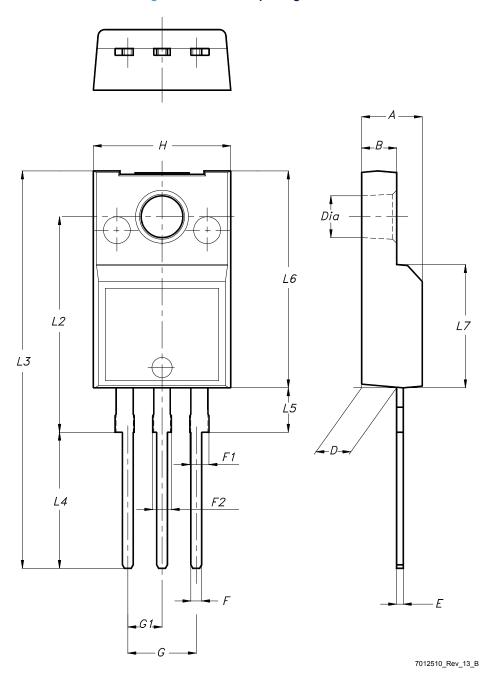


4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220FP package information

Figure 22. TO-220FP package outline



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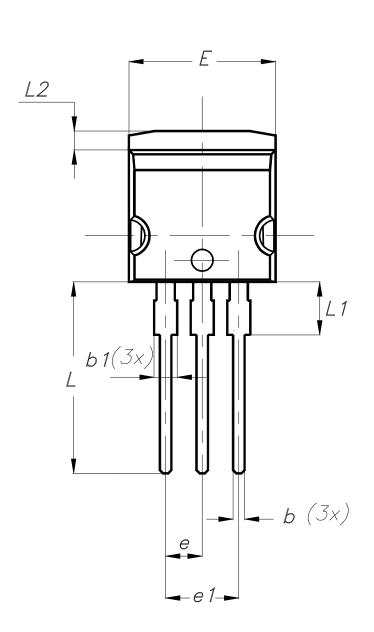
Table 8. TO-220FP package mechanical data

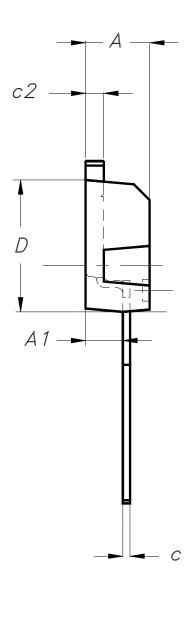
| Dim. | mm | | | | |
|--------|-------|-------|-------|--|--|
| Dilli. | Min. | Тур. | Max. | | |
| А | 4.40 | | 4.60 | | |
| В | 2.50 | | 2.70 | | |
| D | 2.50 | | 2.75 | | |
| Е | 0.45 | | 0.70 | | |
| F | 0.75 | | 1.00 | | |
| F1 | 1.15 | | 1.70 | | |
| F2 | 1.15 | | 1.70 | | |
| G | 4.95 | | 5.20 | | |
| G1 | 2.40 | | 2.70 | | |
| Н | 10.00 | | 10.40 | | |
| L2 | | 16.00 | | | |
| L3 | 28.60 | | 30.60 | | |
| L4 | 9.80 | | 10.60 | | |
| L5 | 2.90 | | 3.60 | | |
| L6 | 15.90 | | 16.40 | | |
| L7 | 9.00 | | 9.30 | | |
| Dia | 3.00 | | 3.20 | | |



4.2 I²PAK package information

Figure 23. I²PAK package outline





0004982_Rev_9



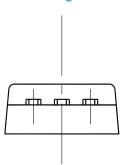
Table 9. I²PAK package mechanical data

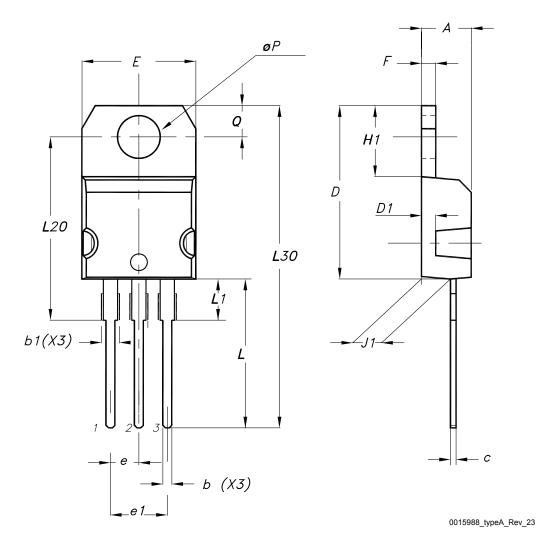
| Dim. | mm | | | | |
|--------|-------|------|-------|--|--|
| Dilli. | Min. | Тур. | Max. | | |
| Α | 4.40 | - | 4.60 | | |
| A1 | 2.40 | - | 2.72 | | |
| b | 0.61 | - | 0.88 | | |
| b1 | 1.14 | - | 1.70 | | |
| С | 0.49 | - | 0.70 | | |
| c2 | 1.23 | - | 1.32 | | |
| D | 8.95 | - | 9.35 | | |
| е | 2.40 | - | 2.70 | | |
| e1 | 4.95 | - | 5.15 | | |
| Е | 10.00 | - | 10.40 | | |
| L | 13.00 | - | 14.00 | | |
| L1 | 3.50 | - | 3.93 | | |
| L2 | 1.27 | - | 1.40 | | |



4.3 TO-220 type A package information

Figure 24. TO-220 type A package outline





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Table 10. TO-220 type A package mechanical data

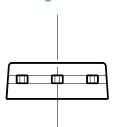
| Dim. | | mm | |
|---------------|-------|-------|-------|
| Dim. | Min. | Тур. | Max. |
| Α | 4.40 | | 4.60 |
| b | 0.61 | | 0.88 |
| b1 | 1.14 | | 1.55 |
| С | 0.48 | | 0.70 |
| D | 15.25 | | 15.75 |
| D1 | | 1.27 | |
| Е | 10.00 | | 10.40 |
| е | 2.40 | | 2.70 |
| e1 | 4.95 | | 5.15 |
| F | 1.23 | | 1.32 |
| H1 | 6.20 | | 6.60 |
| J1 | 2.40 | | 2.72 |
| L | 13.00 | | 14.00 |
| L1 | 3.50 | | 3.93 |
| L20 | | 16.40 | |
| L30 | | 28.90 | |
| ØΡ | 3.75 | | 3.85 |
| Q | 2.65 | | 2.95 |
| Slug flatness | | 0.03 | 0.10 |

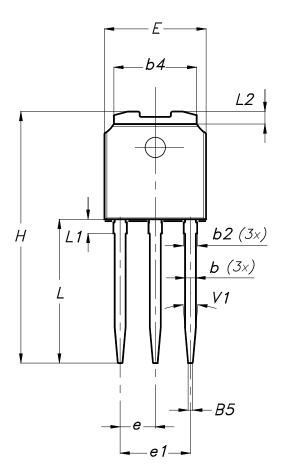
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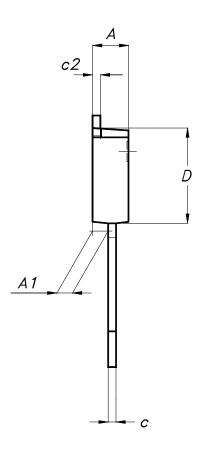


4.4 IPAK (TO-251) type A package information

Figure 25. IPAK (TO-251) type A package outline







0068771_IK_typeA_rev15

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Table 11. IPAK (TO-251) type A package mechanical data

| Dim. | | mm | | | | |
|--------|------|-------|------|--|--|--|
| Dilli. | Min. | Тур. | Max. | | | |
| Α | 2.20 | | 2.40 | | | |
| A1 | 0.90 | | 1.10 | | | |
| b | 0.64 | | 0.90 | | | |
| b2 | | | 0.95 | | | |
| b4 | 5.20 | | 5.40 | | | |
| B5 | | 0.30 | | | | |
| С | 0.45 | | 0.60 | | | |
| c2 | 0.48 | | 0.60 | | | |
| D | 6.00 | | 6.20 | | | |
| E | 6.40 | | 6.60 | | | |
| е | | 2.28 | | | | |
| e1 | 4.40 | | 4.60 | | | |
| Н | | 16.10 | | | | |
| L | 9.00 | | 9.40 | | | |
| L1 | 0.80 | | 1.20 | | | |
| L2 | | 0.80 | 1.00 | | | |
| V1 | | 10° | | | | |



5 Ordering information

Table 12. Order codes

| Order codes | Marking | Package | Packing |
|-------------|-----------|--------------------|---------|
| STF13NM60N | | TO-220FP | |
| STI13NM60N | 12NIM60NI | I ² PAK | Tube |
| STP13NM60N | 13NM60N | TO-220 | Tube |
| STU13NM60N | | IPAK | |

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Revision history

Table 13. Document revision history

| Date | Revision | Changes |
|--------------|----------|---|
| 29-Feb-2009 | 1 | First release |
| 13-Jan-2010 | 2 | - Added new package, mechanical data: TO-247 |
| | | Added new package, mechanical data: D²PAK |
| 29-Feb-2009 | 3 | - Modified Figure 4 |
| 00-1100-2010 | | – Added new package, mechanical data: I²PAK |
| 10 lon 2012 | 4 | - Added new package, mechanical data: IPAK |
| 10-Jaii-2012 | | - Minor text changes |
| 14-Nov-2012 | 5 | The part numbers STB13NM60N and STD13NM60N have been moved to a separate datasheet. |
| | | Section 4: Package mechanical data has been updated. |
| | | The part number STW13NM60N have been moved to a separate datasheet and the document has been updated accordingly. |
| | 6 | Updated cover page. |
| 26-Oct-2020 | | Updated Section 1 Electrical ratings. |
| | | Updated Table 4. Static and Table 7. Source-drain diode. |
| | | Updated Section 4 Package information. |
| | | Added Section 5 Ordering information. |
| | | Minor text changes. |



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| Re | Revision history | | | | | |



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